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NPN SILICON HIGH SPEED SWITHCHING TRANSISTORS

P2N2369



TO-92 Plastic Package

LOW POWER FOR HIGH SPEED SWITCHING APPLICATIONS

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	VALUE	UI	NIT
			- 1:- m	
Collector Emitter Voltage	V _{CEO}	15	T-TP CON	V
Collector Base Voltage	V _{CBO}	40	0750	V
Collector Emitter Voltage (V _{BE} =0)	V _{CES}	40		V
Emitter Base Voltage	V _{EBO}	4.5	,	V
Collector Current Peak	I _{CM}	500	m	nΑ
Power Dissipation @ Ta=25°C	P _D com	625	m	ıW
Operating And Storage Junction	T_j , T_{stg}	-55 to +150	0	C
Tempera <mark>ture Range</mark>	10.7			
THERMAL RESISTANCE			1	
Junction to Ambient in free air	R _{th(j-a)}	200	C C	;/W
		I FE VIII	ALW.	





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ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

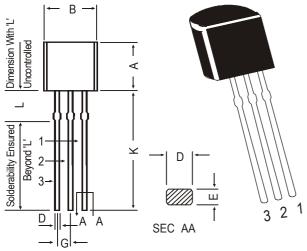
DECORIDEION	OVMDOL	TEGT COMPLTION	VA	UNIT		
DESCRIPTION	SYMBOL	TEST CONDITION	MIN	IN MAX		
Collector Emitter Breakdown Voltage	BV _{CEO}	$I_C=10$ mA, $I_B=0$	15		V	
Collector Emitter Breakdown Voltage	BV _{CES}	$I_{C}=10\mu A, V_{BE}=0$	40		V	
Collector Base Breakdown Voltage	BV _{CBO}	$I_{C}=10\mu A, I_{E}=0$	40		V	
Emitter Base Breakdown Voltage	BV _{EBO}	$I_E=10\mu A, I_C=0$	4.5		V	
Collector Leakage Current	I _{CBO}	$V_{CB}=20V$, $I_{E}=0$		400	nA	
Collector Leakage Current	I _{CBO}	V _{CB} =20V, Ta=125°C		30	μΑ	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	I _C =10mA, I _B =1mA		0.25	V	
Base Emitter Saturation Voltage	$V_{BE(sat)}$	I _C =10mA, I _B =1mA	0.7	0.85	V	
DC Current Gain	h _{FE}	I _C =10mA, V _{CE} =1V	40	120		
		I _C =100mA, V _{CE} =2V*	20			
		I _C =10mA, V _{CE} =1V,	20			
		Ta= -55°C				
DYNAMIC CHARACTERISTICS						
Output Capacitance	C _c	$I_E=0, V_{CB}=5V$		4	pF	
		f=140KHz				
Small Signal Current Gain	h _{fe}	$V_{CE} = 10V, I_{C} = 10mA$	5		MHz	
		f=100MH _Z				
SWITCHING CHARCTERISTICS						
Turn on Time	t _{on}	I _C =10mA, I _{B1} =3mA,		12	ns	
		V _{CC} =3V				
Turn off Time	t _{off}	I _C =10mA, I _{B1} =3mA,		18	ns	
	-	V _{CC} =3V,I _{B2} =1.5mA				
Storage Time	t _s	I _C =10mA, I _{B1} =10mA= I _{B2}		13	ns	

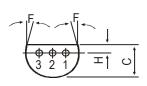
^{*}Pulse Condition: Length \leq 300ms, Duty Cycle \leq 2%.

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TO-92 Transistors on Tape and Ammo Pack TO-92 Transistors on Tape and Ammo Pack



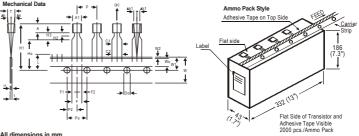


PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

DIM	MIN.	MAX.			
Α	4.32	5.33			
В	4.45	5.20 4.19			
С	3.18				
D	0.41	0.55 0.50 EG			
Е	0.35				
F	5 DI				
G	1.14	1.40			
Н	1.14	1.53			
K	12.70	_			
L	1.982	2.082			

All diminsions in mm.



All dimensions in mm						2000 pcs./Allillo i dck
		SPECIFICATION				
ITEM	SYMBOL	MIN.	NOM.	MAX.	TOL.	REMARKS
BODY WIDTH	A1	4.0		4.8		
BODY HEIGHT	A	4.8		5.2		
BODY THICKNESS	T	3.9		4.2		
PITCH OF COMPONENT	P		12.7		± 1.0	
FEED HOLE PITCH	Po		12.7		± 0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
FEED HOLE CENTRE TO						
COMPONENT CENTRE	P2		6.35		± 0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER						
LEADS	F		5.08		+ 0.6 - 0.2	
COMPONENT ALIGNMENT SIDE VIEW	Δh		0	1.0	- 0.2	AT TOP OF BODY
COMPONENT ALIGNMENT FRONT VIEW			0	1.3		AT TOP OF BODY
TAPE WIDTH	w w		18		± 0.5	
HOLD-DOWN TAPE WIDTH	Wo		6		± 0.2	
HOLE POSITION	W1		9		+ 0.7	
					- 0.5	
HOLD-DOWN TAPE POSITION	W2		0.5		± 0.2	
LEAD WIRE CLINCH HEIGHT	Ho		16		± 0.5	
COMPONENT HEIGHT	H1			23.25		
LENGTH OF SNIPPED LEADS	L			11.0		
FEED HOLE DIAMETER	Do		4		± 0.2	
TOTAL TAPE THICKNESS	t			1.2		t1 0.3-0.6
LEAD - TO - LEAD DISTANCE	F1, F2		2.54		+ 0.4	
STAND OFF	H2	0.45		1.45	- 0.1	
CLINCH HEIGHT	H3	0.45		3.0		
LEAD PARALLELISM	1 C1 - C2 I			0.22		
PULL - OUT FORCE	(P)	6N		0.22		
TOLL - OUT FOROL	1 (*)	JUN	1			

- NOTES

 1. Maximum alignment deviation between leads will not to be greater than 0.2mm.

 2. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.

 3. Holddown tape will not exceed beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.

 4. There will be no more than three (3) consecutive missing components in a tape.

 5. A tape traiter, having at least three feed holes are provided after the last component in a tape.

 6. Splices should not interfere with the sprocket feed holes.

Packing Detail

<u> </u>										
PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX					
	Details Net Weight / Qty		Size	Qty	Size	Qty	Gr Wt			
TO-92 Bulk	1K/polybag	200 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	23 kgs			
TO-92 T&A	2K/ammo box	645 gm/2K pcs	12.5" x 8" x 1.8"	2K	17" x 15" x 13.5"	32K	12.5 kgs			

Notes P2N2369

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Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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CDIL is a registered Trademark of
Continental Device India Limited
C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com